L Number	Hits	Search Text	DB	Time stamp
229	2955	(groove or trench) and (die or chip) and etch$3 and (saw$3 or dic$3)	USPAT; EPO; JPO; IBM_TDB	2003/12/17 13:53
230	2382	((groove or trench) and (die or chip) and etch$3 and (saw$3 or dic$3)) and semiconductor	USPAT; EPO; JPO; DERWENT	2003/12/17 13:53
231	1184	(groove or trench) same etch$3 same (saw$3 or dic$3)	USPAT; EPO; JPO; IBM_TDB	2003/12/17 16:39
232	757	((groove or trench) same etch$3 same (saw$3 or dic$3)) and semiconductor	USPAT; EPO; JPO; DERWENT	2003/12/17 15:04
233	8	(((groove or trench) same etch$3 same (saw$3 or dic$3)) and semiconductor) and (etch adj second)	USPAT; EPO; JPO; DERWENT	2003/12/17 13:56
234	161	(((groove or trench) same etch$3 same (saw$3 or dic$3)) and semiconductor) and (oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT	2003/12/17 13:57
235	1		USPAT	2003/12/17 14:22
236	195	((groove or trench) same die same etch$3) and (saw$3 or dic$3)	USPAT; EPO; JPO; IBM_TDB	2003/12/17 14:25
249	1		USPAT	2003/12/17 14:55
250	757	((groove or trench) same etch$3 same (saw$3 or dic$3)) and semiconductor	USPAT; EPO; JPO; DERWENT	2003/12/17 16:26
251	9	(groove or trench) same etch$3 same SF6 same (oxygen or "O.sub.2")	USPAT; EPO; JPO; IBM_TDB	2003/12/17 16:22
252	603	(groove or trench) same etch$3 same saw$3	USPAT; EPO; JPO; IBM_TDB	2003/12/17 17:12
253	334	((groove or trench) same etch$3 same saw$3) and semiconductor	USPAT; EPO; JPO; DERWENT	2003/12/17 16:26
254	784	(groove or trench) same etch$3 same dic$3	USPAT; EPO; JPO; IBM_TDB	2003/12/17 16:40
255	590	((groove or trench) same etch$3 same dic$3) and wafer	USPAT; EPO; JPO; IBM_TDB	2003/12/17 16:41
256	609	(groove or trench) same etch$3 same dicing	USPAT; EPO; JPO; IBM_TDB	2003/12/17 17:13